

Excellent Integrated System Limited

Stocking Distributor

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Vishay/Siliconix SI7960DP-T1-E3

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Si7960DP

Vishay Siliconix

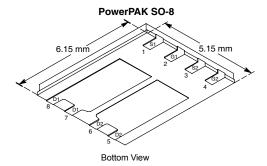
Dual N-Channel 60-V (D-S) MOSFET

PRODUCT SUMMARY				
V _{DS} (V)	$R_{DS(on)}\left(\Omega\right)$	I _D (A)		
60	0.021 at V _{GS} = 10 V	9.7		
	0.025 at V _{GS} = 4.5 V	8.9		

FEATURES

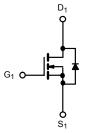
- Halogen-free According to IEC 61249-2-21 Available
- TrenchFET[®] Power MOSFET
- New Low Thermal Resistance PowerPAK[®] Package
- Dual MOSFET for Space Savings



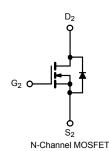


Ordering Information: Si7960DP-T1-E3 (Lead (Pb)-free)

Si7960DP-T1-GE3 (Lead (Pb)-free and Halogen-free)



N-Channel MOSFET



ABSOLUTE MAXIMUM RATINGS	T _A = 25 °C, unles	ss otherwise n	oted		
Parameter		Symbol	10 s	Steady State	Unit
Drain-Source Voltage		V_{DS}	60		V
Gate-Source Voltage		V_{GS}	± 20		
Continuous Drain Current (T _{.I} = 150 °C) ^a	T _A = 25 °C	I _D	9.7	6.2	
Continuous Drain Current (1) = 150 °C)	T _A = 70 °C		7.8	5.0	
Pulsed Drain Current		I _{DM}	40		Α
Continuous Source Current (Diode Conduction) ^a		I _S	2.9	1.2	
Single Avalanche Current	L = 0.1 mH	I _{AS}	23		
Single Avalanche Energy		E _{AS}	27		mJ
M	T _A = 25 °C	P _D	3.5	1.4	W
Maximum Power Dissipation ^a	T _A = 70 °C		2.2	0.9	VV
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to 150		°C
Soldering Recommendations (Peak Temperature)b, c			260		

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient ^a	t ≤ 10 s	R _{thJA}	26	35	°C/W
Maximum Junction-to-Ambient	Steady State		60	85	
Maximum Junction-to-Case (Drain)	Steady State	R_{thJC}	2.2	2.7	

Notes:

- a. Surface Mounted on 1" x 1" FR4 board.
- b. See Solder Profile (www.vishay.com/ppg?73257). The PowerPAK SO-8 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
- c. Rework Conditions: manual soldering with a soldering iron is not recommended for leadless components.

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Datasheet of SI7960DP-T1-E3 - MOSFET 2N-CH 60V 6.2A PPAK SO-8

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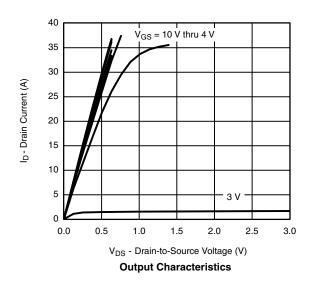


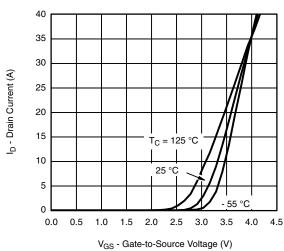
Parameter	Symbol	Test Conditions M		Тур.	Max.	Unit	
Static			•	•			
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_D = 250 \mu\text{A}$ 1			3	V	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			± 100	nA	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 60 V, V _{GS} = 0 V			1		
		$V_{DS} = 60 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55 ^{\circ}\text{C}$	J = 55 °C		5	μΑ	
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \ge 5 \text{ V}, V_{GS} = 10 \text{ V}$	30			Α	
Drain-Source On-State Resistance ^a		$V_{GS} = 10 \text{ V}, I_D = 9.7 \text{ A}$		0.017	0.021		
	R _{DS(on)}	$V_{GS} = 4.5 \text{ V}, I_D = 8.9 \text{ A}$	0.020		0.025	Ω	
Forward Transconductance ^a	9 _{fs}	$V_{DS} = 15 \text{ V}, I_{D} = 9.7 \text{ A}$		33		S	
Diode Forward Voltage ^a	V_{SD}	$I_S = 2.9 \text{ A}, V_{GS} = 0 \text{ V}$		0.8	1.2	V	
Dynamic ^b	<u> </u>		•	1			
Total Gate Charge	Q_g			49	75	nC	
Gate-Source Charge	Q _{gs}	$V_{DS} = 30 \text{ V}, V_{GS} = 10 \text{ V}, I_{D} = 9.7 \text{ A}$		5.7			
Gate-Drain Charge	Q _{gd}			8.6			
Gate Resistance	R_g	f = 1 MHz		2		Ω	
Turn-On Delay Time	t _{d(on)}			12	20		
Rise Time	t _r	V_{DD} = 30 V, R_L = 30 Ω		12	20	ns	
Turn-Off Delay Time	t _{d(off)}	$I_D \cong 1 \text{ A}, V_{GEN} = 10 \text{ V}, R_G = 6 \Omega$		60	90		
Fall Time	t _f			17	30		
Source-Drain Reverse Recovery Time	t _{rr}	I _F = 2.9 A, dI/dt = 100 A/μs		30	60		

Notes

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted





Transfer Characteristics

a. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %. b. Guaranteed by design, not subject to production testing.

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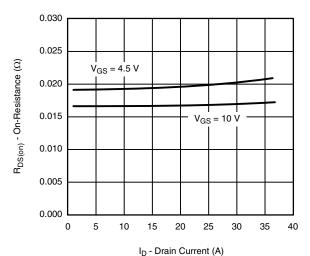




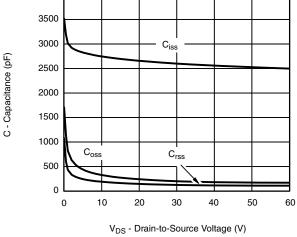
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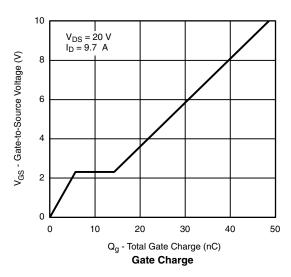
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



On-Resistance vs. Drain Current

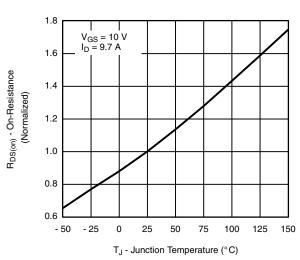


Capacitance

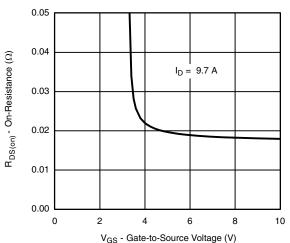


T_J = 150 °C I_S - Source Current (A) 10 T_{.J} = 25 °C 0.0 0.2 0.4 1.0 1.2

V_{SD} - Source-to-Drain Voltage (V) Source-Drain Diode Forward Voltage



On-Resistance vs. Junction Temperature



On-Resistance vs. Gate-to-Source Voltage

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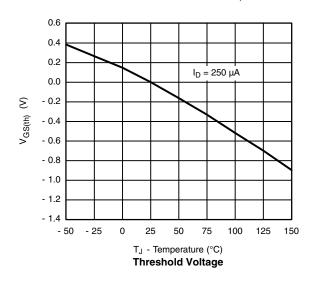
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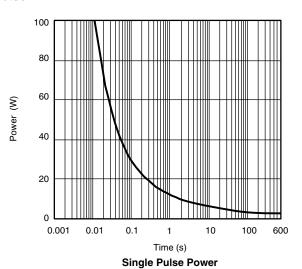


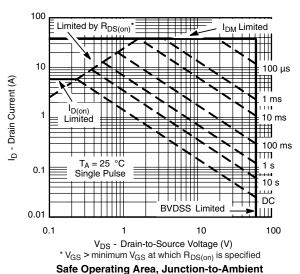
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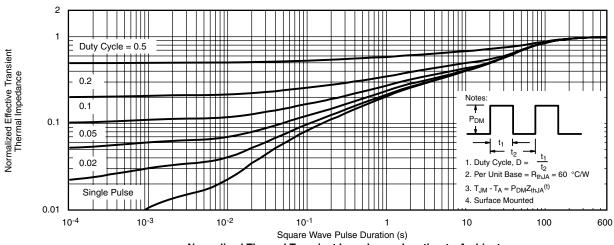
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TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted









Normalized Thermal Transient Impedance, Junction-to-Ambient

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Datasheet of SI7960DP-T1-E3 - MOSFET 2N-CH 60V 6.2A PPAK SO-8

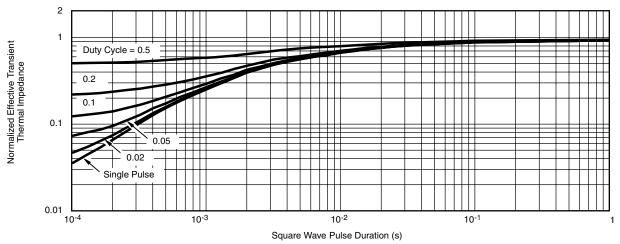
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TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Normalized Thermal Transient Impedance, Junction-to-Case

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?73075.

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Datasheet of SI7960DP-T1-E3 - MOSFET 2N-CH 60V 6.2A PPAK SO-8

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